

ABSTRACT OF THE DISCLOSURE

The invention includes a semiconductor processing method wherein an insulative mass is formed across a first electrical node and a second electrical node. The mass has a pair of openings extending therethrough to the electrical nodes. The individual openings each have a periphery defined by one of the electrical nodes and at least one sidewall. One of the openings extends to the first electrical node and is a first opening, and the other of the openings extends to the second electrical node and is a second opening. A dielectric material layer is formed within the openings to narrow the openings. Conductive material plugs are formed within the narrowed openings. The conductive material plug within the first opening is a first material plug, and is separated from the first electrical node by the dielectric material; and the conductive plug within the second opening is a second material plug, and is not separated from the second electrical node by the dielectric material. The invention also includes a semiconductor assembly comprising an anti-fuse construction and an electrically conductive interconnect construction.

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